



Description

- Material AlInGap/GaAs Sub
- Structure QW Structure/DBR
- Electrode Au alloy
- Chip Size 620X400 μm (dicing pitch)
- Thickness 250 +/-30 μm
- Surface P type
- Window Size 50 +/-20 μm

Electro-Optical Characteristics(Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITION
Forward Voltage	V _f	--	2.5		V	I _f =50mA
Reverse Current	I _r	--	--	10	μA	V _r -3V
Output Power	P _o	--	0.5	--	mW	I _f =50mA
Peak Wavelength	λ_P	--	650	--	nm	I _f =50mA
Spectral width	λ_D	--	5	--	nm	I _f =50mA
Cutoff frequency	f _c	--	200	--	MHz	I _f =50+/-20mA _{app}

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